

Young Dong Kim

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

37 papers	373 citations	9 h-index	18 g-index
39 ext. papers	578 ext. citations	2.2 avg, IF	3.04 L-index

#	Paper	IF	Citations
37	Azimuthal angle dependent dielectric function of SnS by ellipsometry. <i>Journal of the Korean Physical Society</i> , 2022 , 80, 59-62	0.6	
36	A Systematic Study of Compositionally Dependent Dielectric Tensors of SnS _x Se _{1-x} Alloys by Spectroscopic Ellipsometry. <i>Crystals</i> , 2021 , 11, 548	2.3	2
35	Maximum-entropy revisited: Optimal filtering of spectra. <i>Journal of Applied Physics</i> , 2021 , 129, 224902	2.5	1
34	Modeling the temperature dependence of the optical properties of anisotropic SnS _{0.52} Se _{0.48} . <i>Journal of the Korean Physical Society</i> , 2021 , 78, 269-274	0.6	
33	Approximated dielectric tensor of the biaxial ESnSe crystal. <i>Journal of the Korean Physical Society</i> , 2021 , 78, 297-301	0.6	
32	Quantitative assessment of linear noise-reduction filters for spectroscopy. <i>Optics Express</i> , 2020 , 28, 38913-38933	17.3	38933
31	Modeling of the Temperature Dependence of the Dielectric Function of Biaxial ESnS. <i>Journal of the Korean Physical Society</i> , 2020 , 77, 987-990	0.6	
30	Optical Properties of Anisotropic SnS _x Se _{1-x} for Arbitrary Compositions. <i>Journal of the Korean Physical Society</i> , 2020 , 77, 1178-1182	0.6	2
29	Dielectric Function and Critical Points of SnS _{0.52} Se _{0.48} in the Temperature Range from 27 to 350 K. <i>Journal of the Korean Physical Society</i> , 2020 , 77, 981-986	0.6	1
28	Extended Gaussian Filtering for Noise Reduction in Spectral Analysis. <i>Journal of the Korean Physical Society</i> , 2020 , 77, 819-823	0.6	4
27	Anisotropic behavior of excitons in single-crystal ESnS. <i>AIP Advances</i> , 2020 , 10, 105003	1.5	7
26	Temperature dependence of the dielectric function and critical points of ESnS from 27 to 350K. <i>Scientific Reports</i> , 2020 , 10, 18396	4.9	3
25	Bandgap engineering of two-dimensional semiconductor materials. <i>Npj 2D Materials and Applications</i> , 2020 , 4,	8.8	152
24	Modeling of the Optical Properties of Monolayer WS ₂ . <i>Journal of the Korean Physical Society</i> , 2020 , 77, 298-302	0.6	1
23	Dielectric Functions and Critical Points of GaAsSb Alloys. <i>Journal of the Korean Physical Society</i> , 2019 , 74, 595-599	0.6	3
22	Temperature Dependence of the Dielectric Function of Monolayer MoSe. <i>Scientific Reports</i> , 2018 , 8, 31734	4.9	10
21	How a Fano Resonance Crosses the Mobility Edge in Quantum Waveguides. <i>Journal of Experimental and Theoretical Physics</i> , 2018 , 126, 705-711	1	1

20	Reinforcement of interfacial adhesion of a coated polymer layer on a cobalt-chromium surface for drug-eluting stents. <i>Langmuir</i> , 2014 , 30, 8020-8	4	20
19	Interband transitions and dielectric functions of InGaSb alloys. <i>Applied Physics Letters</i> , 2013 , 102, 102109	3.4	5
18	Optical properties of AlAs _x Sb _{1-x} alloys determined by in situ ellipsometry. <i>Applied Physics Letters</i> , 2013 , 103, 011901	3.4	4
17	Lattice constants and optical response of pseudomorph Si-rich SiGe:B. <i>Applied Physics Letters</i> , 2013 , 103, 202107	3.4	1
16	Optical properties of solution-processed LaAlO _x /Si films using spectroscopic ellipsometry. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 04D110	1.3	3
15	Temperature-dependent optical properties of epitaxial CdO thin films determined by spectroscopic ellipsometry and Raman scattering. <i>Journal of Applied Physics</i> , 2013 , 113, 183515	2.5	9
14	Formation of self-assembled large droplet-epitaxial GaAs islands for the application to reduced reflection. <i>Journal of Applied Physics</i> , 2013 , 113, 154308	2.5	7
13	Study of the interaction between HSA and oligo-DNA using total internal reflection ellipsometry. <i>Journal of the Korean Physical Society</i> , 2012 , 60, 1288-1291	0.6	2
12	Study of the Interaction Between Biomolecule Monolayers Using Total Internal Reflection Ellipsometry. <i>Journal of the Korean Physical Society</i> , 2011 , 58, 1031-1034	0.6	5
11	Dielectric functions and interband transitions of In _{1-x} Al _x Sb alloys. <i>Applied Physics Letters</i> , 2010 , 97, 111902	3.4	6
10	Interband transitions of InAs _x Sb _{1-x} alloy films. <i>Applied Physics Letters</i> , 2009 , 95, 111902	3.4	23
9	Dielectric response of AlSb from 0.7 to 5.0 eV determined by in situ ellipsometry. <i>Applied Physics Letters</i> , 2009 , 94, 231913	3.4	13
8	Optical properties of In _x Al _{1-x} As alloy films. <i>Applied Physics Letters</i> , 2008 , 92, 151907	3.4	13
7	Overlayer effects in the critical-point analysis of ellipsometric spectra: Application to In _x Ga _{1-x} As alloys. <i>Journal of Applied Physics</i> , 2008 , 103, 073502	2.5	4
6	Model dielectric functions for Al _x Ga _{1-x} As alloys of arbitrary compositions. <i>Journal of Applied Physics</i> , 2008 , 104, 013515	2.5	13
5	Dielectric properties of InAsP alloy thin films and evaluation of direct- and reciprocal-space methods of determining critical-point parameters. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 884-887	1.6	3
4	Optical properties of Co silicides: Experiment and density functional theory. <i>Journal of Applied Physics</i> , 2007 , 102, 103503	2.5	6
3	Dielectric Functions of CdSe and ZnSe Obtained by Using Vacuum Ultra-Violet Spectroscopic Ellipsometry. <i>Journal of the Korean Physical Society</i> , 2007 , 50, 806	0.6	5

- 2 Dielectric functions of In_xGa_{1-x}As alloys. *Physical Review B*, **2003**, 68, 3.3 39
- 1 Surface photoabsorption monitoring of the growth of GaAs and InGaAs at 650°C by MOCVD. *Journal of Electronic Materials*, **1997**, 26, 1164-1168 1.9 2